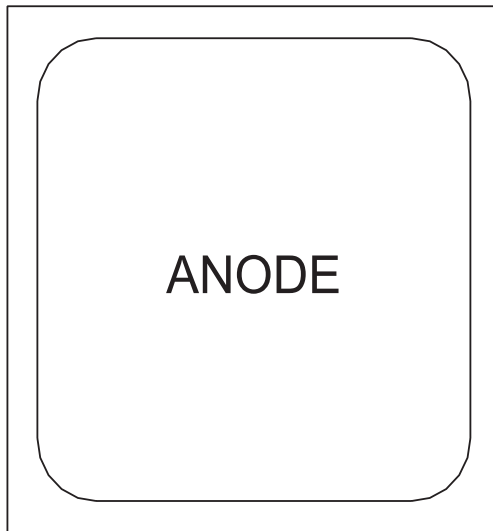


**PROCESS DETAILS**

Process	GLASS PASSIVATED MESA
Die Size	87 x 87 MILS
Die Thickness	10.6 MILS
Anode Bonding Pad Area	69.5 x 69.5 MILS
Top Side Metalization	Au - 5,000Å
Back Side Metalization	Au - 2,000Å

**GEOMETRY**



BACKSIDE CATHODE

R0

145 Adams Avenue  
Hauppauge, NY 11788 USA  
Tel: (631) 435-1110  
Fax: (631) 435-1824  
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**GROSS DIE PER 4 INCH WAFER**

1,490

**PRINCIPAL DEVICE TYPES**

1N5185 thru 1N5188  
1N5415 thru 1N5420

The Typical Electrical Characteristics data for this chip is currently being revised.

For the latest updated data for this Chip Process, please visit our website at:

[www.centrasemi.com/chip](http://www.centrasemi.com/chip)

R1 (1-August 2002)